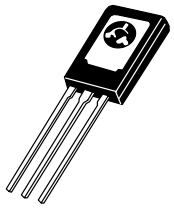
MJE350

Plastic Medium Power PNP Silicon Transistor

. . . designed for use in line–operated applications such as low power, line–operated series pass and switching regulators requiring PNP capability.

- High Collector–Emitter Sustaining Voltage —
  $V_{CEO(sus)}$ = 300 Vdc @ I_C = 1.0 mAdc
- Excellent DC Current Gain —
  h_{FE} = 30–240 @ I_C = 50 mAdc
- Plastic Thermopad Package

0.5 AMPERE
POWER TRANSISTOR
PNP SILICON
300 VOLTS
20 WATTS



CASE 77–09
TO–225AA TYPE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	300	Vdc
Emitter–Base Voltage	V_{EB}	3.0	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	20 0.16	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	6.25	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{CEO(sus)}$	300	—	Vdc
Collector Cutoff Current (V_{CB} = 300 Vdc, I_E = 0)	I_{CBO}	—	100	μAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	100	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 50 mAdc, V_{CE} = 10 Vdc)	h_{FE}	30	240	—

June, 2001 – Rev. 11
Publication Order Number:
MJE350/D

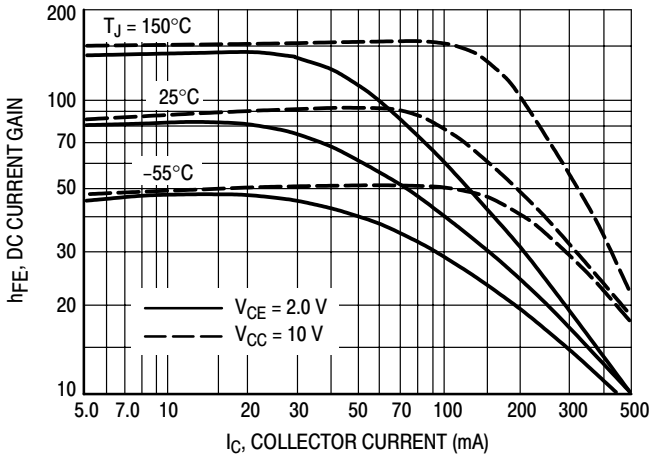


Figure 1. DC Current Gain

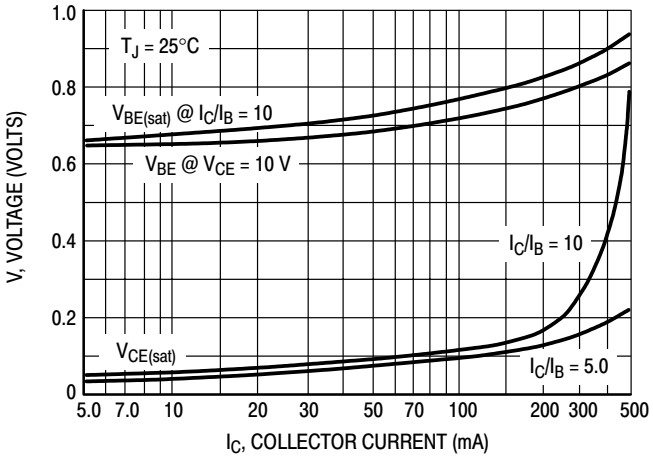


Figure 2. "On" Voltages

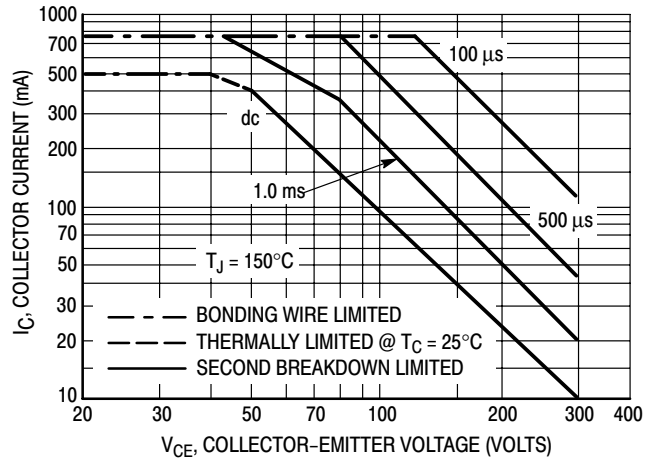


Figure 3. Active−Region Safe Operating Area

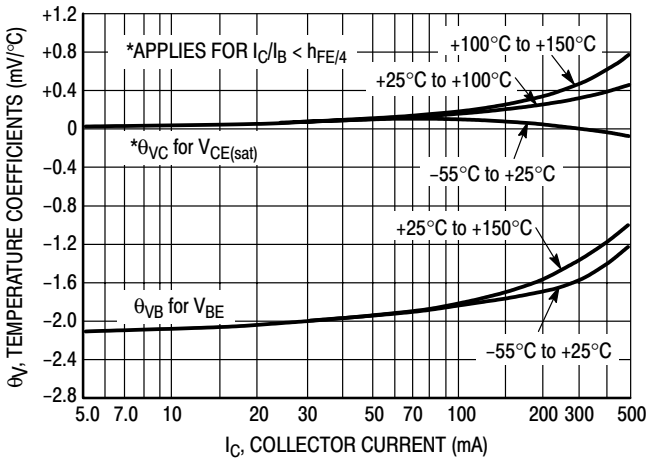


Figure 4. Temperature Coefficients

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 3 is based on $T_{J(pk)}$ = 150°C; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq$ 150°C. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

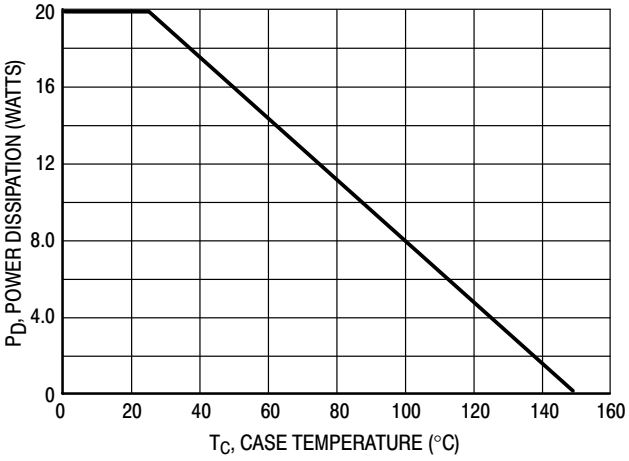
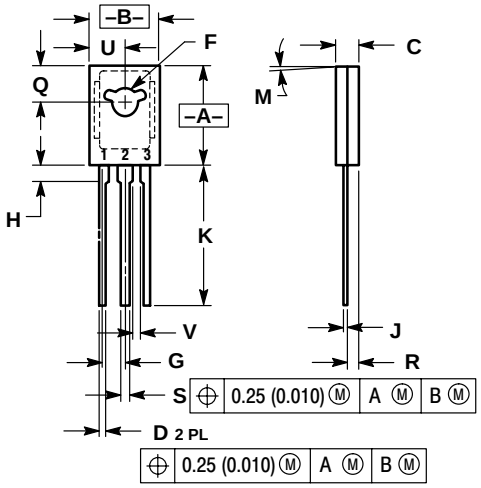


Figure 5. Power Derating

PACKAGE DIMENSIONS

TO−225
CASE 77−09
ISSUE W



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

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